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## Reduction of HfZrO<sub>2</sub> capacitor wake-up effect

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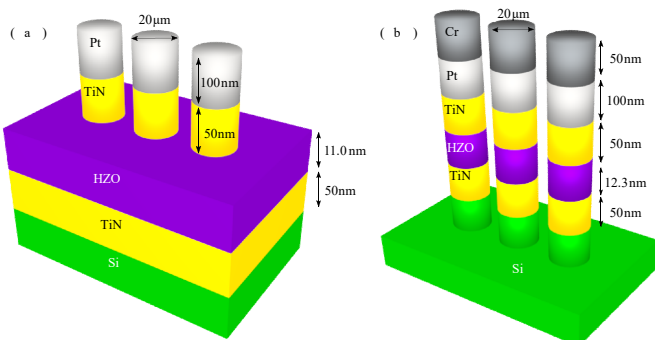
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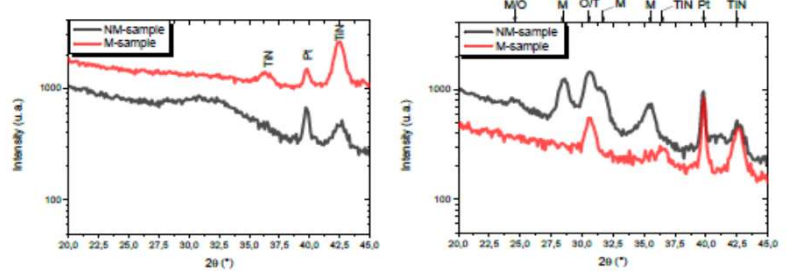
Wake-up effect is a major issue for ferroelectric HfO<sub>2</sub>-based memory devices. Here, two TiN/Hf<sub>0.5</sub>Zr<sub>0.5</sub>O<sub>2</sub>/TiN structures deposited by magnetron sputtering on silicon are compared. The maximum remanant polarization is higher than 21 μC/cm<sup>2</sup> for both samples, a strong difference is observed in the electrical behavior. For the mesa sample, the difference between maximal and initial Pr is only 3 μC/cm<sup>2</sup> whereas it is around 14 μC/cm<sup>2</sup> in the non-mesa case. We discuss the root causes of these behaviors in light of structural results. Various applications have been suggested for fluorite-structure ferroelectrics due to their advantages over the conventional perovskite-structure ferroelectrics. In this presentation we will focus on (Hf,Zr)O<sub>2</sub> (HZO) thin films deposition for the capacitor of Ferroelectric Random Access Memories (FRAM) in the 1Transistor-1Capacitor (1T-1C) model. (Hf,Zr)O<sub>2</sub> thin films are studied to either fully understand the stabilization of the ferroelectric phase (f-phase) or to fit with industrial requirements. Samples are stacks of Si/TiN/Hf<sub>0.5</sub>Zr<sub>0.5</sub>O<sub>2</sub>/TiN/Pt. All materials are grown by sputtering at room temperature following by a rapid thermal annealing at 450°C during 30 seconds under N<sub>2</sub> atmosphere. The samples are called NM, and M. NM and M refers to two different architectures, respectively non-mesa and mesa structures.

## Samples structures



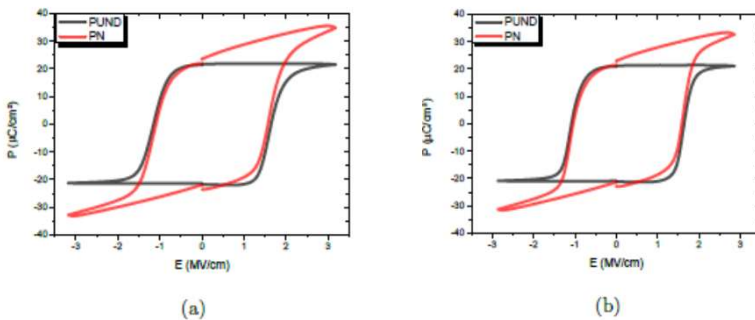
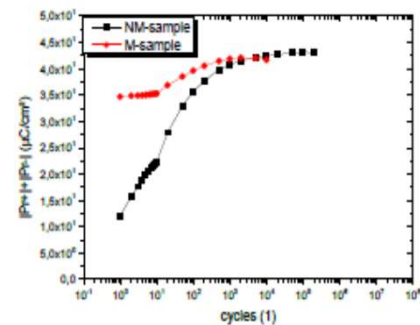
Schemes of (a) NM-sample and (b) M-sample

## Grazing Incident X-Ray Diffraction



GIXRD measurements comparing NM-sample (black curve) and M-sample (red curve) (a) before RTA (b) after RTA. M stands for monoclinic, O for orthorhombic and T for tetragonal phases

## Electrical characterizations PUND, PN, cycling


 Polarization versus applied electrical field for (a) NM-sample at 10<sup>5</sup> cycles (b) M-sample at 2.10<sup>3</sup> cycles under the stress conditions: 2.5 kHz and 3.5 V

 Change of  $|P_{r+}| + |P_{r-}|$  versus the number of cycles with the stress conditions 2.5 kHz and 3.5 V for NM-sample (black curve) and M-sample (red curve)

We report the fabrication of two samples deposited by magnetron sputtering with excellent performances, quite similar to samples deposited by Atomic Layer Deposition.  $P_r$  values are among the highest for samples deposited by sputtering. Although the N-sample and NM-samples show very close  $P_r$  values, the two samples show completely different electrical behaviors. During cycling, the increase of  $P_r$  value for the NM-sample is more than an order of magnitude higher than the M-sample. It is accompanied by a decrease of the endurance which is two orders of magnitude higher for the NM-sample than for the M-sample. As electrical behaviors are not the same, for low stress conditions M-sample has a higher  $P_r$  value during cycling whereas for high stress conditions NM-sample has a higher  $P_r$  value during cycling. As a matter of fact, it has been proven that maximum  $P_r$  values are more sensitive to stress conditions than the structures themselves. The origins of the different electrical behaviors come from the micro-crystalline structures of the two samples, according to GIXRD results. The crystallization takes place during the annealing step. During annealing, M-sample is built with a TiN TE fully covering the HZO layer whereas the TiN covers only partially the HZO layer in case of the NM-sample. It induces different stress states which lead to two different micro-crystalline patterning. The M-sample shows no monoclinic peak, whereas the NM-sample shows many monoclinic orientations. It can explain the huge reduction of the wake-up effect.